

Silicon Carbide (SiC)
MOSFET – EliteSiC,
 19 mohm, 650 V, M2,
 TO-247-4L

NTH4L025N065SC1

Features

- Typ. $R_{DS(on)} = 19\text{ m}\Omega$ @ $V_{GS} = 18\text{ V}$
 Typ. $R_{DS(on)} = 25\text{ m}\Omega$ @ $V_{GS} = 15\text{ V}$
- Ultra Low Gate Charge ($Q_{G(tot)} = 164\text{ nC}$)
- Low Capacitance ($C_{OSS} = 278\text{ pF}$)
- 100% Avalanche Tested
- $T_J = 175^\circ\text{C}$
- This Device is Halide Free and RoHS Compliant with exemption 7a,
 Pb-Free 2LI (on second level interconnection)

Typical Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Power Supplies)
- Energy Storages

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
"			

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DISTANCE MAXIMUM RATINGS

Parameter	Symbol	Max	Unit
	θ		°
	θ		

CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

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ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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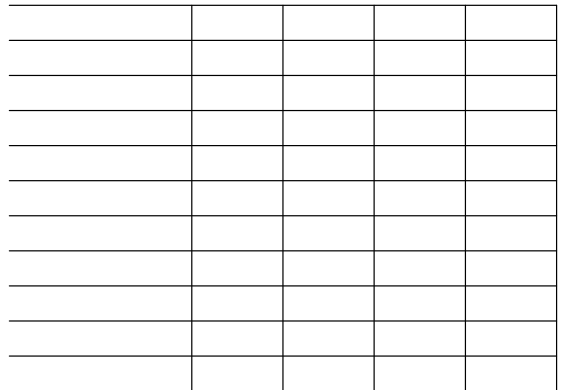
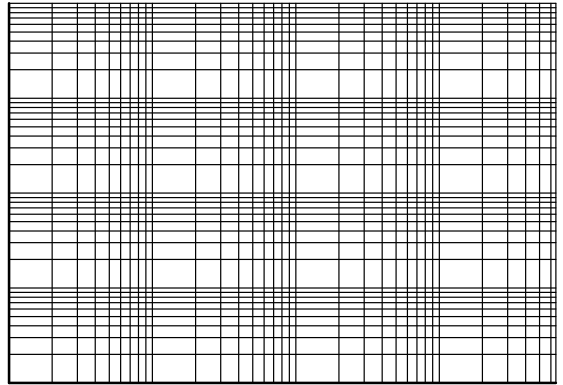
DRAIN-SOURCE DIODE CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
		μ				
						μ

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TYPICAL CHARACTERISTICS



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TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019

A E A B
A2 E1 \emptyset p1
D2

E/2 Q

D D1

\emptyset

L1

b2 A1

b1 (3X) L

1 4

e1 b(4X) c

e 2X

\oplus 0.254 (M) B A (M)

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